National Semiconductor

NMC93CS06/CS26/CS46 256-Bit/512-Bit/1024-Bit Serial Electrically Erasable Programmable Memories

General Description

The NMC93CS06/NMC93CS26/NMC93CS46 are 256/512/1024 bits of read/write memory divided into 16/32/64 registers of 16 bits each. N registers (N ≤ 16, N ≤ 32 or N ≤ 64) can be protected against data modification by programming into a special on-chip register called the memory protect register the address of the first register to be protected. This address can be locked into the device, so that these registers can be permanently protected. Thereafter, all attempts to alter data in a register whose address is equal to or greater than the address stored in the protect register will be aborted.

The read instruction loads the address of the first register to be read into a 6-bit address pointer. Then the data is clocked out serially on the D0 pin and automatically cycles to the next register to produce a serial data stream. In this way the entire memory can be read in one continuous data stream or as registers of varying length from 16 to 256/512/1024 bits. Thus, the NMC93CS06/NMC93CS26/NMC93CS46 can be viewed as a non-volatile shift register.

The write cycle is completely self-timed. No separate erase cycle is required before write. The write cycle is only enabled when pin 6 (program enable) is held high. If the address of the register to be written is less than the address

in the protect register then the data is written 16 bits at a time into one of the 16/32/64 data registers. If CS is brought high following the initiation of a write cycle the D0 pin indicates the ready/busy status of the chip.

National Semiconductor's EEPROMs are designed and tested for applications requiring extended endurance. Refer to device operation for further endurance information. Data retention is specified to be greater than 10 years.

Features

■ Write protection in user defined section of memory
■ Typical active current 400 μA; Typical standby current 25 μA
■ Reliable CMOS floating gate technology
■ 5 volt only operation in all modes
■ Microwire compatible serial I/O
■ Self-timed programming cycle
■ Device status signal during programming mode
■ Sequential register read
■ Over 10 years data retention
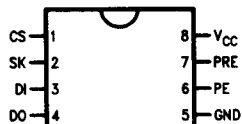■ 40,000 write cycles typical

Block Diagram
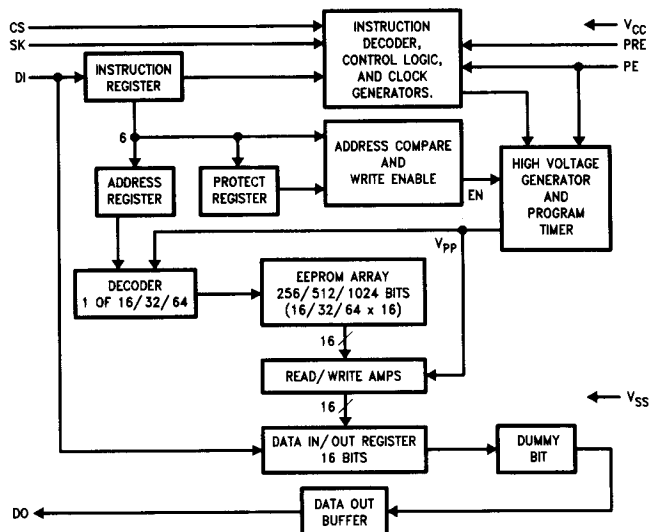
TL/D/9208-3

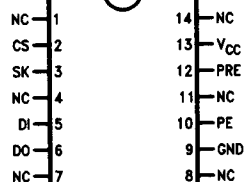# Connection Diagrams

PIN OUT:

Dual-In-Line Package (N)

```
        ┌───┬───┐
CS  ──│1      8│── VCC
SK  ──│2      7│── PRE
DI  ──│3      6│── PE
DO  ──│4      5│── GND
        └───────┘
```

TL/D/9208–1

Top View

See NS Package Number N08E

Pin Names	
CS	Chip Select
SK	Serial Data Clock
DI	Serial Data Input
DO	Serial Data Output
GND	Ground
PE	Program Enable
PRE	Protect Register Enable
V_{CC}	Power Supply

PIN OUT:

SO Package (M)

```
        ┌───┬───┐
NC  ──│1     14│── NC
CS  ──│2     13│── VCC
SK  ──│3     12│── PRE
NC  ──│4     11│── NC
DI  ──│5     10│── PE
DO  ──│6      9│── GND
NC  ──│7      8│── NC
        └───────┘
```

TL/D/9208–2

Top View

See NS Package Number M14A

Ordering Information

Commercial Temp. Range (0°C to +70°C)
$V_{CC} = 5V \pm 10\%$

Order Number
NMC93CS06N/NMC93CS26N/
NMC93CS46N
NMC93CS06M/NMC93CS26M/
NMC93CS46M

Extended Temp. Range (−40°C to +85°C)
$V_{CC} = 5V \pm 10\%$

Order Number
NMC93CS06EN/NMC93CS26EN/
NMC93CS46EN
NMC93CS06EM/NMC93CS26EM/
NMC93CS46EM

Military Temp. Range (−55°C to +125°C)

Order Number
NMC93CS06MN/NMC93CS26MN/
NMC93CS46MN
NMC93CS06MM/NMC93CS26MM/
NMC93CS46MM

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Ambient Storage Temperature	−65°C to +150°C
All Input or Output Voltages with Respect to Ground	+6.5V to −0.3V
Lead Temperature (Soldering, 10 sec.)	+300°C
ESD rating	2000V

Operating Conditions

Ambient Operating Temperature
NMC93CS06/NMC93CS26/ NMC93CS46	0°C to +70°C
NMC93CS06E/NMC93CS26E/ NMC93CS46E	−40°C to +85°C
NMC93CS06M/NMC93CS26M/ NMC93CS46M (Mil. Temp.)	−55°C to +125°C
Positive Power Supply	4.5V to 5.5V

DC and AC Electrical Characteristics V_{CC} = 5V ±10% unless otherwise specified

Symbol	Parameter	Part Number	Conditions	Min	Max	Units
I_{CC1}	Operating Current CMOS Input Levels	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M*	CS = V_{IH}, SK = 1 MHz SK = 0.5 MHz SK = 0.5 MHz		2 2 2	mA
I_{CC2}	Operating Current TTL Input Levels	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	CS = V_{IH}, SK = 1 MHz SK = 0.5 MHz SK = 0.5 MHz		3 3 4	mA
I_{CC3}	Standby Current	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	CS = 0V		50 100 100	μA
I_{IL}	Input Leakage	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	V_{IN} = 0V to V_{CC}	−2.5 −10 −10	2.5 10 10	μA
I_{OL}	Output Leakage	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	V_{OUT} = 0V to V_{CC}	−2.5 −10 −10	2.5 10 10	μA
V_{IL} V_{IH}	Input Low Voltage Input High Voltage			−0.1 2	0.8 V_{CC} + 1	V
V_{OL1} V_{OH1}	Output Low Voltage Output High Voltage		I_{OL} = 2.1 mA I_{OH} = −400 μA	2.4	0.4	V
V_{OL2} V_{OH2}	Output Low Voltage Output High Voltage		I_{OL} = 10 μA I_{OH} = −10 μA	V_{CC} − 0.2	0.2	V
f_{SK}	SK Clock Frequency	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M		0 0 0	1 0.5 0.5	MHz
t_{SKH}	SK High Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	(Note 2) (Note 3) (Note 3)	250 500 500		ns
t_{SKL}	SK Low Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	(Note 2) (Note 3) (Note 3)	250 500 500		ns
t_{CS}	Minimum CS Low Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	(Note 4) (Note 5) (Note 5)	250 500 500		ns
t_{CSS}	CS Setup Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	Relative to SK	50 100 100		ns
t_{PRES}	PRE Setup Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	Relative to SK	50 100 100		ns

*Throughout this table "M" refers to temperature range (−55°C to +125°C), not package.

DC and AC Electrical Characteristics $V_{CC} = 5V \pm 10\%$ unless otherwise specified (Continued)

Symbol	Parameter	Part Number	Conditions	Min	Max	Units
t_{PES}	PE Setup Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	Relative to SK	50 100 100		ns
t_{DIS}	DI Setup Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	Relative to SK	100 200 200		ns
t_{CSH}	CS Hold Time		Relative to SK	0		ns
t_{PEH}	PE Hold Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	Relative to CS Relative to CS Relative to CS	250 500 500		ns
t_{PREH}	PRE Hold Time		Relative to SK	0		ns
t_{DIH}	DI Hold Time	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	Relative to SK	100 200 200		ns
t_{PD1}	Output Delay to "1"	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	AC Test		500 1000 1000	ns
t_{PD0}	Output Delay to "0"	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	AC Test		500 1000 1000	ns
t_{SV}	CS to Status Valid	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	AC Test		500 1000 1000	ns
t_{DF}	CS to DO in TRI-STATE®	NMC93CS06/NMC93CS26/NMC93CS46 NMC93CS06E/NMC93CS26E/NMC93CS46E NMC93CS06M/NMC93CS26M/NMC93CS46M	$CS = V_{IL}$ AC Test		100 200 200	ns
t_{WP}	Write Cycle Time				10	ms
	Endurance		Number of Data Changes per Bit	Typical 40,000		Cycles

Note 1: Stress above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note 2: The SK frequency specification for Commercial parts specifies a minimum SK clock period of 1 microsecond, therefore in an SK clock cycle $t_{SKH} + t_{SKL}$ must be greater than or equal to 1 microsecond. For example if $t_{SKL} = 250$ ns then the minimum $t_{SKH} = 750$ ns in order to meet the SK frequency specification.

Note 3: The SK frequency specification for Extended Temperature and Military parts specifies a minimum SK clock period of 2 microseconds, therefore in an SK clock cycle $t_{SKH} + t_{SKL}$ must be greater than or equal to 2 microseconds. For example, if $t_{SKL} = 500$ ns then the minimum $t_{SKH} = 1.5$ microseconds in order to meet the SK frequency specification.

Note 4: For Commercial parts CS must be brought low for a minimum of 250 ns (t_{CS}) between consecutive instruction cycles.

Note 5: For Extended Temperature and Military parts CS must be brought low for a minimum of 500 ns (t_{CS}) between consecutive instruction cycles.

Note 6: This parameter is periodically sampled and not 100% tested.

Capacitance (Note 6)
$T_A = 25°C$, $f = 1MHz$

Symbol	Test	Typ	Max	Units
C_{OUT}	Output Capacitance		5	pF
C_{IN}	Input Capacitance		5	pF

AC Test Conditions

Output Load	1 TTL Gate and $C_L = 100$ pF
Input Pulse Levels	0.4V to 2.4V
Timing Measurement Reference Level	
Input	1V and 2V
Output	0.8V and 2V

3-22

Functional Description

The NMC93CS06, NMC93CS26, and NMC93CS46 have 10 instructions as described below. Note that the MSB of any instruction is a "1" and is viewed as a start bit in the interface sequence. The next 8-bits carry the op code and the 6-bit address for selection of 1 of 16, 32, or 64 16-bit registers.

Read (READ):

The Read (READ) instruction outputs serial data on the D0 pin. After a READ instruction is received, the instruction and address are decoded, followed by data transfer from the selected memory register into a 16-bit serial-out shift register. A dummy bit (logical 0) precedes the 16-bit data output string. Output data changes are initiated by a low to high transition of the SK clock. In the NONVOLATILE SHIFT-REGISTER mode of operation, the memory automatically cycles to the next register after each 16 data bits are clocked out. The dummy-bit is suppressed in this mode and a continuous string of data is obtained.

Write Enable (WEN):

When V_{CC} is applied to the part, it "powers up" in the Write Disable (WDS) state. Therefore, all programming modes must be preceded by a Write Enable (WEN) instruction. Once a Write Enable instruction is executed programming remains enabled until a Write Disable (WDS) instruction is executed or V_{CC} is removed from the part.

Write (WRITE):

The Write (WRITE) instruction is followed by 16 bits of data to be written into the specified address. After the last bit of data (D0) is put on the data-in (DI) pin, CS must be brought low before the next rising edge of the SK clock. This falling edge of the CS initiates the self-timed programming cycle. The PE pin **MUST** be held high while loading the WRITE instruction, however, after loading the WRITE instruction the PE pin becomes a "don't care". The D0 pin indicates the READY/BUSY status of the chip if CS is brought high after a minimum of 250 ns (t_{CS}). D0 = logical 0 indicates that programming is still in progress. D0 = logical 1 indicates

that the register at the address specified in the instruction has been written with the data pattern specified in the instruction and the part is ready for another instruction.

Write All (WRALL):

The Write All (WRALL) instruction is valid only when the Protect Register has been cleared by executing a PRCLEAR instruction. The WRALL instruction will simultaneously program all registers with the data pattern specified in the instruction. Like the WRITE instruction, the PE pin **MUST** be held high while loading the WRALL instruction, however, after loading the WRITE instruction the PE pin becomes a "don't care". As in the WRITE mode, the DO pin indicates the READY/BUSY status of the chip if CS is brought high after a minimum of 250 ns (t_{CS}).

Write Disable (WDS):

To protect against accidental data disturb, the Write Disable (WDS) instruction disables all programming modes and should follow all programming operations. Execution of a READ instruction is independent of both the WEN and WDS instructions.

Protect Register Read (PRREAD):

The Protect Register Read (PRREAD) instruction outputs the address stored in the Protect Register on the DO pin. The PRE pin **MUST** be held high while loading the instruction. Following the PRREAD instruction the 6-bit address stored in the memory protect register is transferred to the serial out shift register. As in the READ mode, a dummy bit (logical 0) precedes the 6-bit address string.

Protect Register Enable (PREN):

The Protect Register Enable (PREN) instruction is used to enable the PRCLEAR, PRWRITE, and PRDS modes. Before the PREN mode can be entered, the part must be in the Write Enable (WEN) mode. Both the PRE and PE pins **MUST** be held high while loading the instruction.

Note that a PREN instruction must **immediately** precede a PRCLEAR, PRWRITE, or PRDS instruction.

Instruction Set for the NMC93CS06, NMC93CS26 and NMC93CS46

Instruction	SB	Op Code	Address	Data	PRE	PE	Comments
READ	1	10	A5–A0		0	X	Reads data stored in memory, starting at specified address.
WEN	1	00	11XXXX		0	1	Write enable must precede all programming modes.
WRITE	1	01	A5–A0	D15–D0	0	1	Writes register if address is unprotected.
WRALL	1	00	01XXXX	D15–D0	0	1	Writes all registers. Valid only when Protect Register is cleared.
WDS	1	00	00XXXX		0	X	Disables all programming instructions.
PRREAD	1	10	XXXXXX		1	X	Reads address stored in Protect Register.
PREN	1	00	11XXXX		1	1	Must immediately precede PRCLEAR, PRWRITE, and PRDS instructions.
PRCLEAR	1	11	111111		1	1	Clears the Protect Register so that no registers are protected from WRITE.
PRWRITE	1	01	A5–A0		1	1	Programs address into Protect Register. Thereafter, memory addresses $\geq$ the address in Protect Register are protected from WRITE.
PRDS	1	00	000000		1	1	One time only instruction after which the address in the Protect Register cannot be altered.

3

Functional Description (Continued)

Protect Register Clear (PRCLEAR):

The Protect Register Clear (PRCLEAR) instruction clears the address stored in the Protect Register and, therefore, enables **all** registers for the WRITE and WRALL instruction. The PRE and PE pins **must** be held high while loading the instruction, however, after loading the PRCLEAR instruction the PRE and PE pins become "don't care". Note that a PREN instruction must **immediately** precede a PRCLEAR instruction.

Protect Register Write (PRWRITE):

The Protect Register Write (PRWRITE) instruction is used to write into the Protect Register the address of the first register to be protected. After the PRWRITE instruction is executed, all memory registers whose addresses are greater than or equal to the address specified in the Protect Register are protected from the WRITE operation. Note that before executing a PRWRITE instruction the Protect Register must first be cleared by executing a PRCLEAR operation and that the PRE and PE pins **must** be held high while loading the instruction, however, after loading the PRWRITE instruction the PRE and PE pins become 'don't care'. Note that a PREN instruction must **immediately** precede a PRWRITE instruction.

Protect Register Disable (PRDS):

The Protect Register Disable (PRDS) instruction is a **one** time only instruction which renders the Protect Register unalterable in the future. Therefore, the specified registers become **PERMANENTLY** protected against data changes. As in the PRWRITE instruction the PRE and PE pins **must** be held high while loading the instruction, and after loading the PRDS instruction the PRE and PE pins become "don't care".

Note that a PREN instruction must **immediately** precede a PRDS instruction.
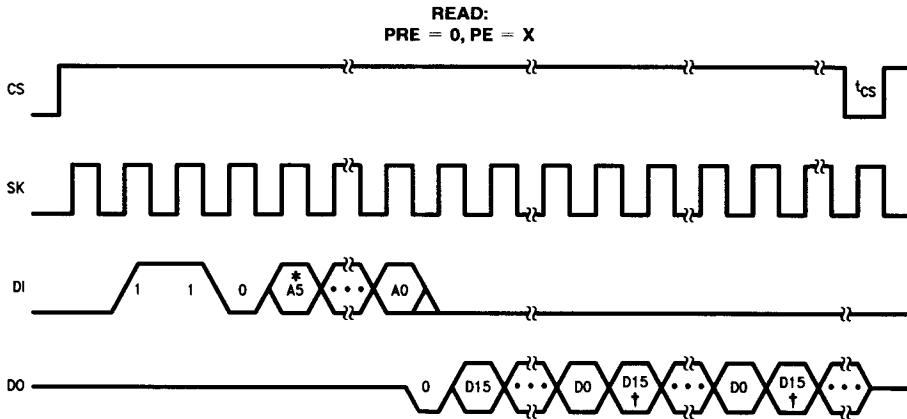
Timing Diagrams

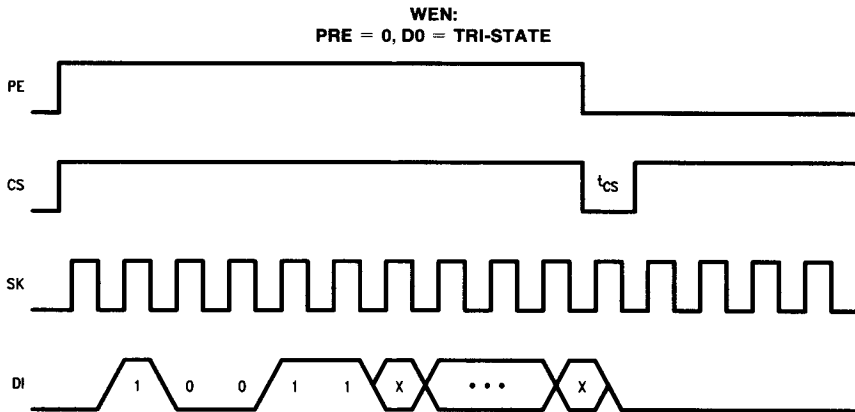### Synchronous Data Timing
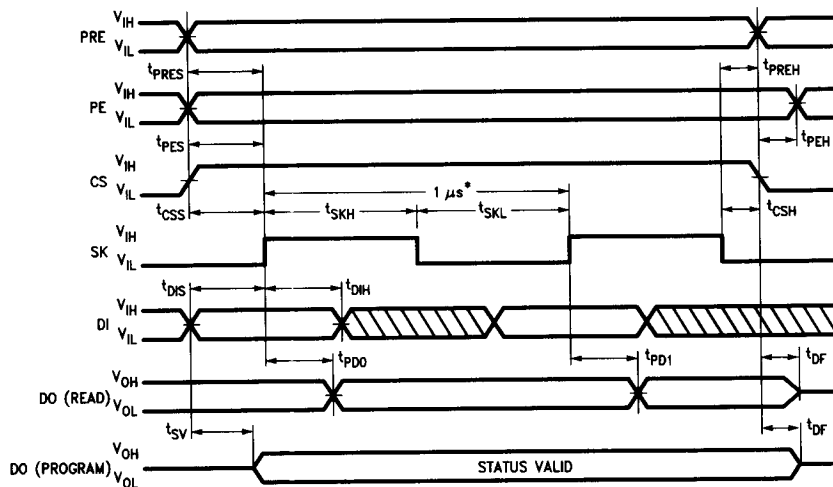
TL/D/9208–4

*This is the minimum SK period (See Note 2).

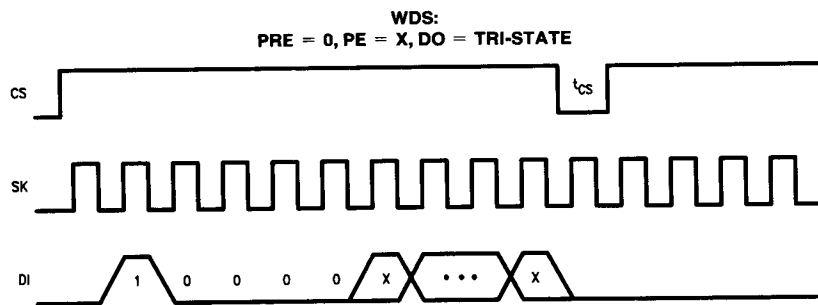# Timing Diagrams (Continued)

READ:
PRE = 0, PE = X

*Address bit A5 becomes a "don't care" for NMC93CS26
*Address bits A5 and A4 become "don't cares" for NMC93CS06
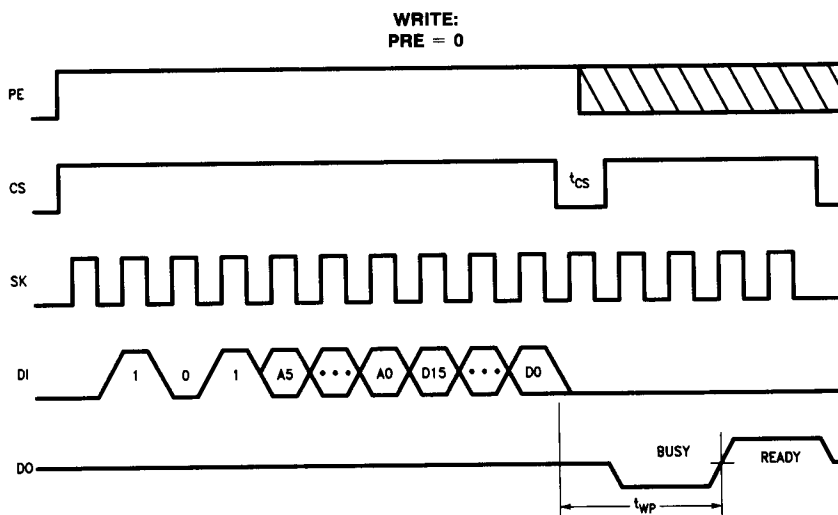†The memory automatically cycles to the next register.

TL/D/9208–5

WEN:
PRE = 0, DO = TRI-STATE

TL/D/9208–6

3

Timing Diagrams (Continued)

WDS:
PRE = 0, PE = X, DO = TRI-STATE
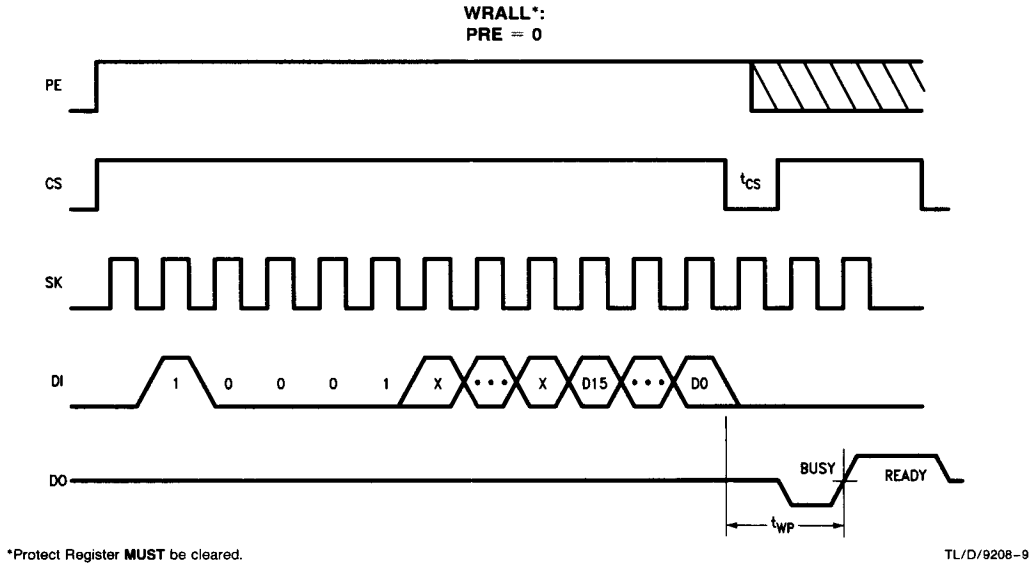

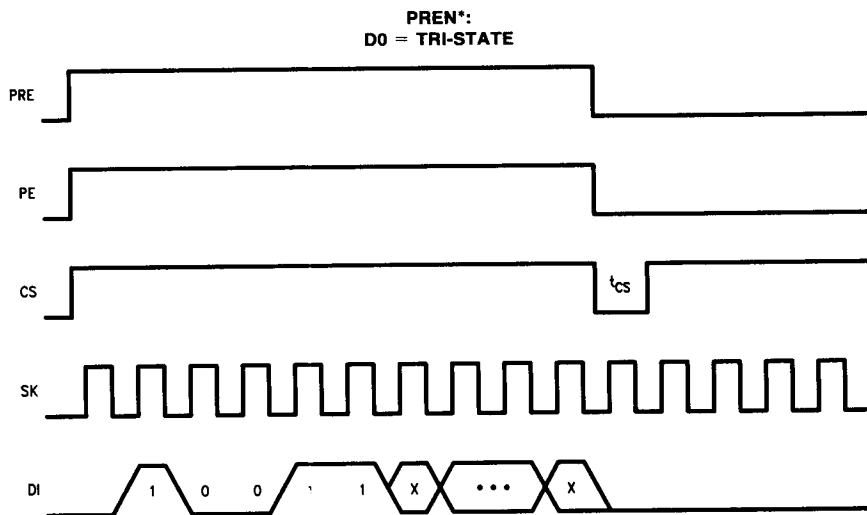TL/D/9208–7

WRITE:
PRE = 0

TL/D/9208–8

- Address bit A5 becomes a "don't care" for NMC93CS26
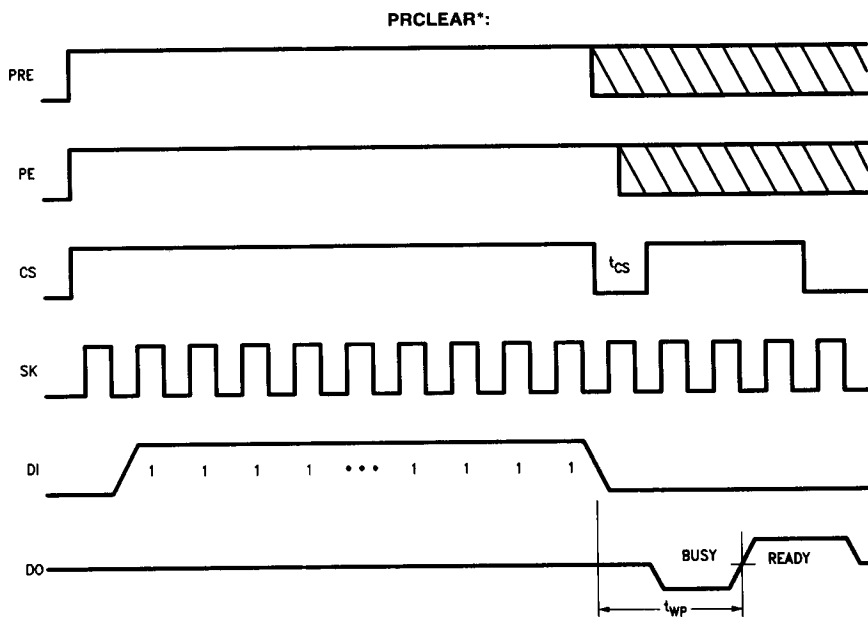- Address bits A5 and A4 become "don't cares" for NMC93CS06

3-26

Timing Diagrams (Continued)

WRALL*:
PRE = 0

PE

CS t_{CS}

SK

DI   1 0 0 0 1 X • • • X D15 • • • D0

DO   BUSY   READY

t_{WP}

*Protect Register **MUST** be cleared.

TL/D/9208–9

PRREAD:
PE = X

PRE

CS t_{CS}

SK

DI   1 1 0 X • • • X

DO   0 A5 A4 • • • A0 • X •

• Address bit A5 becomes a "don't care" for NMC93CS26
• Address bits A5 and A4 become "don't cares" for NMC93CS06

TL/D/9208–10

3

Timing Diagrams (Continued)

PREN*:
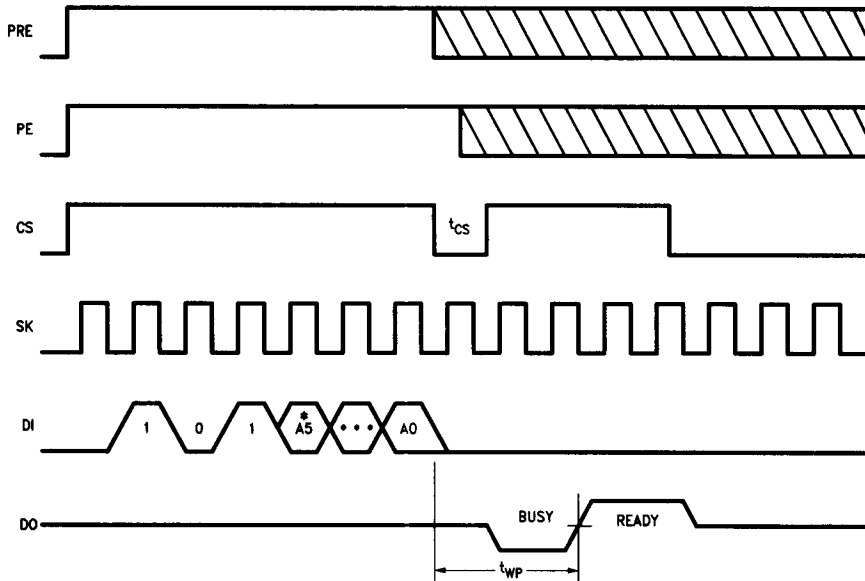**D0 = TRI-STATE**

TL/D/9208-11
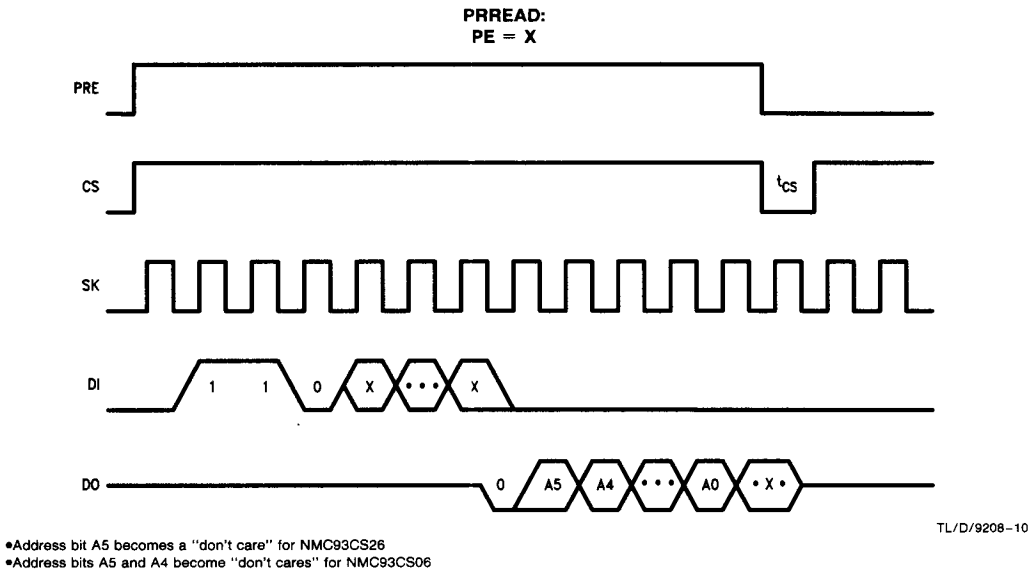
*A WEN cycle must precede a PREN cycle.

PRCLEAR*:

*A PREN cycle must **immediately** precede a PRCLEAR cycle.

TL/D/9208-12
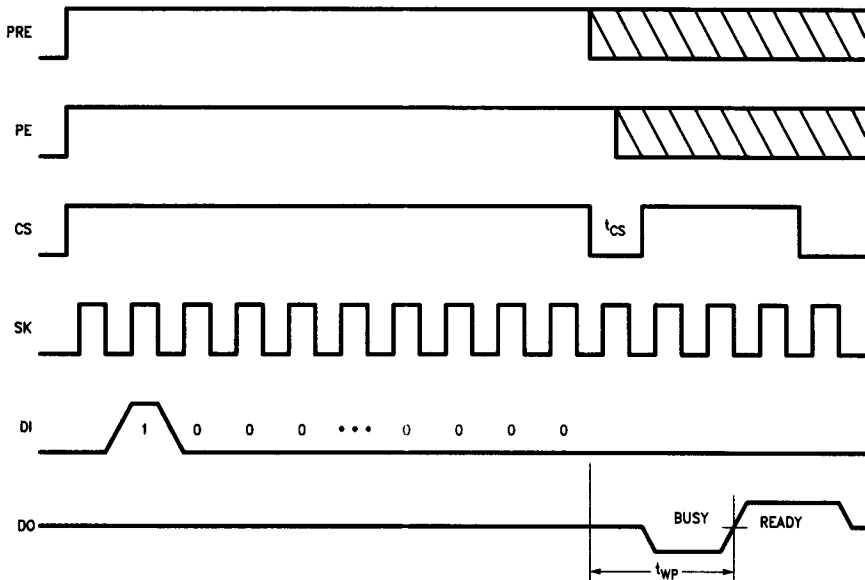
3-28

Timing Diagrams (Continued)

PRWRITE†:

TL/D/9208–13

*Address bit A5 becomes a "don't care" for NMC93CS26
*Address bits A5 and A4 become "don't cares" for NMC93CS06
†Protect Register **MUST** be cleared before a PRWRITE cycle. A PREN cycle must **immediately** precede a PRWRITE cycle.

PRDS*:

TL/D/9208–14

*ONE TIME ONLY instruction. A PREN cycle must **immediately** precede a PRDS cycle.